

# NIMD6001AN

## Dual N-Channel Driver with Diagnostic Output 60 V, 3 A, 110 mΩ

NIMD6001AN is a dual 3 Amp low-side switch with an integrated common disable input and drain diagnostic output. Pulling the Disable pin low will override any applied gate voltages and turn off both FET switches. Should either Drain-Source voltage exceed approximately 50 V, a logic 1 (> 3 V) will be asserted on the Diagnostic/Feedback pin. Internal isolation diodes permit the Disable and Diagnostic/Feedback pins of multiple devices to be interconnected in a “wired-OR” configuration without additional components.

### Features

- $R_{DS(on)}$  110 mΩ Maximum at  $V_{GS} = 10$  V
- Avalanche Energy Specified
- Gate Drive Disable Input
- Drain-Source Voltage Diagnostic Feedback Output
- Electrically Isolated Drains for Low Crosstalk
- Internal Resistors Limit Peak Transient gate Current
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### Applications

- Automotive Injector Driver
- Solenoid / Relay Driver

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage (DC, sustained)	$V_{DSS}$	60	Vdc
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	Vdc
Continuous Drain Current $V_{GS} = 10$ V, $R_{\theta JA} = 55^\circ\text{C/W}$ $V_{GS} = 5.0$ V, $R_{\theta JA} = 55^\circ\text{C/W}$	$I_D$	3.3 3.0	A
Single Pulse Drain Current Pulse duration = 80 $\mu\text{s}$	$I_D$	10	A
Single Pulse Drain-to-Source Avalanche Energy $V_{DD} = 60$ V; $V_{GS} = 10$ V; $I_{PK} = 2.6$ A; $L = 76$ mH; Start $T_J = 25^\circ\text{C}$	$E_{AS}$	258	mJ
Operating Junction Temperature	$T_J$	-55 – 150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 – 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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3.0 AMPERES

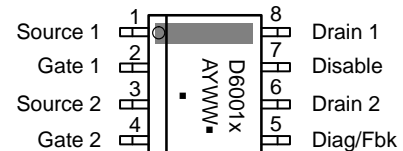
60 VOLTS

$R_{DS(on)} = 110$  mΩ



SOIC-8  
CASE 751

### MARKING DIAGRAM



(Top View)

D6001x = Specific Device Code

x = N or A

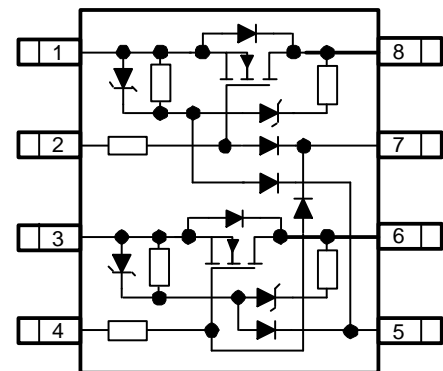
A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)



INTERNAL DIAGRAM

### ORDERING INFORMATION

Device	Package	Shipping†
NIMD6001ANR2G	SOIC-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NIMD6001AN

## PIN DESCRIPTIONS

Pin #	Symbol	Description
1	S1	FET 1 Source and Body
2	G1	FET 1 Gate
3	S2	FET 2 Source and Body
4	G2	FET 2 Gate
5	Diag/Fbk	Diagnostic Feedback – This pin will be logic high when either FET Drain-Source voltage exceeds the Drain Diagnostic threshold.
6	D2	FET 2 Drain
7	Disable	Gate Disable – Pull this pin low to disable both FETs. A logic low will override voltage applied to G1 or G2.
8	D1	FET 1 Drain

## THERMAL RESISTANCE

Parameter	Symbol	Value	Units
Junction-to-Ambient – min. pad footprint (Notes 1 and 2)	$R_{\theta JA}$	96	°C/W
Junction-to-Ambient – 1" Cu pad (Notes 1 and 3)	$R_{\theta JA}$	75	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}; I_D = 5\text{ mA}$	60	67		V
Zero Gate Voltage Drain Current (Note 1)	$I_{DSS}$	$V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}$ $V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}; T_A = 150^\circ\text{C}$		10 80	20 250	$\mu\text{A}$
Gate Input Current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$	-100	$\pm 25$	+100	nA

### ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}; I_D = 250\ \mu\text{A}$	1.0	1.7	3.0	
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}; I_D = 3.3\text{ A}$		60	110	$\text{m}\Omega$
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 5\text{ V}; I_D = 3.0\text{ A}$		72	130	$\text{m}\Omega$

### DYNAMIC CHARACTERISTICS (Note 1)

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V};$ $f = 75\text{ kHz}$		150	175	pF
Output Capacitance	$C_{OSS}$			150	170	
Reverse Transfer Capacitance	$C_{RSS}$			25	30	
Gate Resistance	$R_G$			8	15	$\text{k}\Omega$
Total Gate Charge	$Q_{g(TOT)}$	$V_{GS} = 0\text{ V to } 5\text{ V}; V_{DD} = 30\text{ V};$ $I_D = 3.3\text{ A}; I_G = 1.0\text{ mA},$		8.3	9.0	nC
Gate-to-Source Gate Charge	$Q_{gs}$			1.1	1.6	
Gate-to-Drain Miller Charge	$Q_{gd}$			4.2	5	

1. These values are established by statistical characterization and may not be tested.
2. Surface-mounted on FR4 board using the minimum recommended pad size (Cu area = 40 sq. mm; 1 oz.)
3. Surface-mounted on FR4 board using 1 sq. inch heat spreader (Cu area = 625 sq. mm, 2 oz.)
4. Refer to Figure 1 for definition of switching characteristics symbols.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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### SWITCHING CHARACTERISTICS (Notes 1 and 4)

Turn-On Time	$T_{(on)}$	$V_{GS} = 10\text{ V}; V_{DD} = 30\text{ V};$ $I_D = 3.3\text{ A, Ext. } R_{GS} = 47\ \Omega$		6.0	8.0	$\mu\text{s}$
Turn-On Delay	$T_{d(on)}$			1.7		
Rise Time	$T_r$			3.9		
Turn-Off Time	$T_{(off)}$			24	28	
Turn-Off Delay	$T_{d(off)}$			15		
Fall Time	$T_f$			9.0		

### BODY DIODE

Source-Drain Forward On Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_{SD} = 3.3\text{ A}$		0.85	1.25	V
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### DIAGNOSTIC FEEDBACK (Note 1)

Feedback voltage	$V_{FBK}$	$V_{DS} = 35\text{ V},$ $R_{FBK-SOURCE} = 51\text{ k}\Omega$			1.7	V
Feedback Logical High voltage	$V_{FBK(HI)}$	$V_{DS} = 60\text{ V},$ $R_{FBK-SOURCE} = 51\text{ k}\Omega$	3.0		5.5	V
$V_{DS}$ threshold voltage for logical High	$V_{DSFBK(HI)}$	Ramp $V_{DS}$ positive until $V_{FBK} = 3.5\text{ V}$	45		65	V
$V_{DS}$ threshold voltage for logical Low	$V_{DSFBK(LOW)}$	Ramp $V_{DS}$ negative until $V_{FBK} = 0.8\text{ V}$	25		45	V

### DISABLE (Note 1)

Gate Drive Disable Input Voltage, Gate Enable	$V_{DIS(HI)}$	$V_{DIS} \geq 3.0\text{ V}, V_{GS} = 5\text{ V},$ $I_D = 3.0\text{ A}$	3			V
Gate Drive Disable Input Voltage, Gate Disable	$V_{DIS(LOW)}$	$V_{DIS} \leq 0.4\text{ V}, V_{GS} = V_{DS} = 10\text{ V},$ $I_D \leq 250\ \mu\text{A}; T_J = 150^\circ\text{C}$ (Note 1)			0.4	V

1. These values are established by statistical characterization and may not be tested.
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3. Surface-mounted on FR4 board using 1 sq. inch heat spreader (Cu area = 625 sq. mm, 2 oz.)
4. Refer to Figure 1 for definition of switching characteristics symbols.

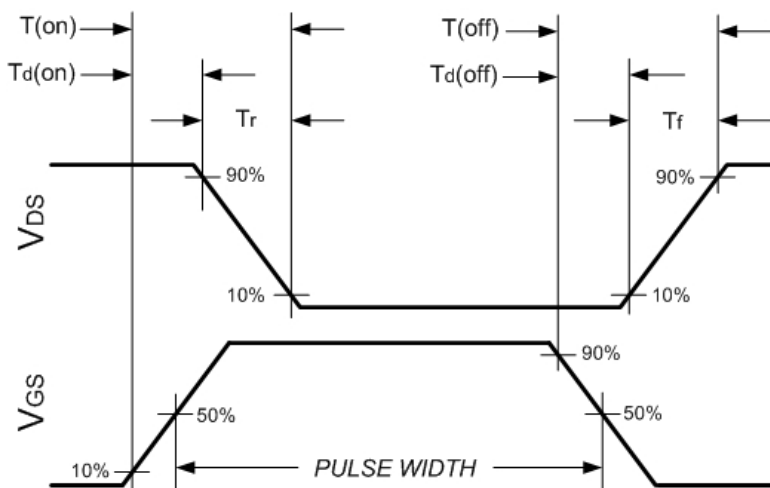


Figure 1. Switching Characteristics Waveforms and Symbols

TYPICAL ELECTRICAL CHARACTERISTICS

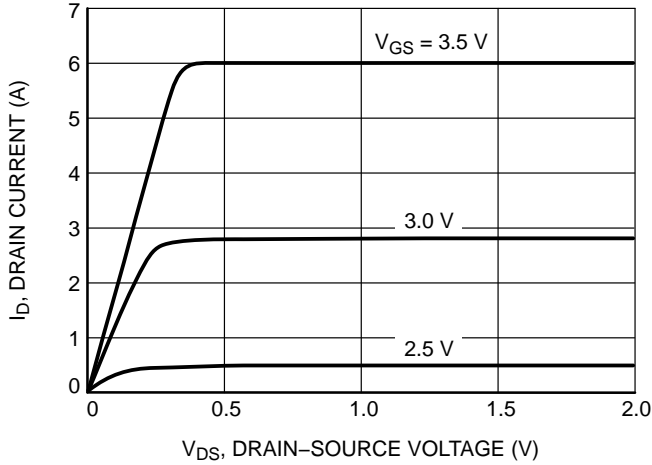


Figure 2. Drain Current vs. Drain-Source Voltage and Gate-Source Voltage

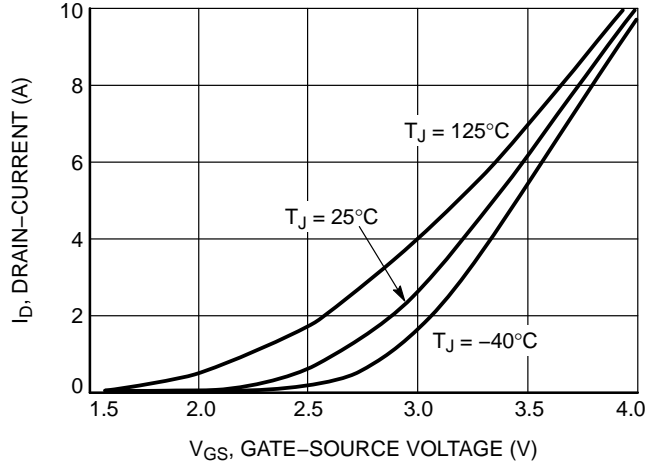


Figure 3. Transfer Function (pulsed). Pulse duration = 80  $\mu$ s, duty cycle < 0.5%;  $V_{DS} = 2$  V

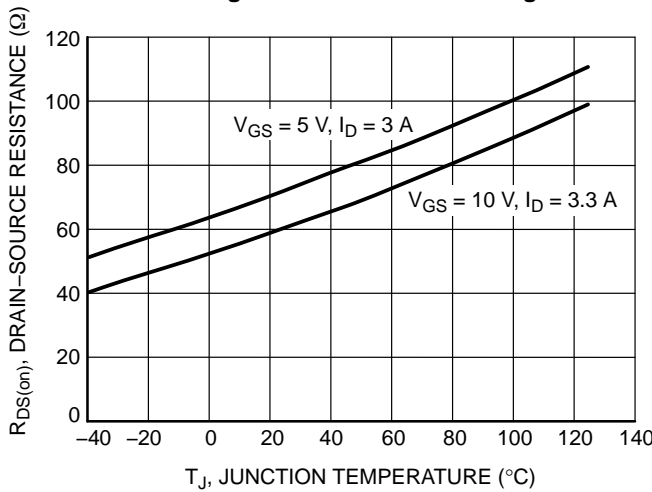


Figure 4. Drain-Source On Resistance vs. Junction Temperature

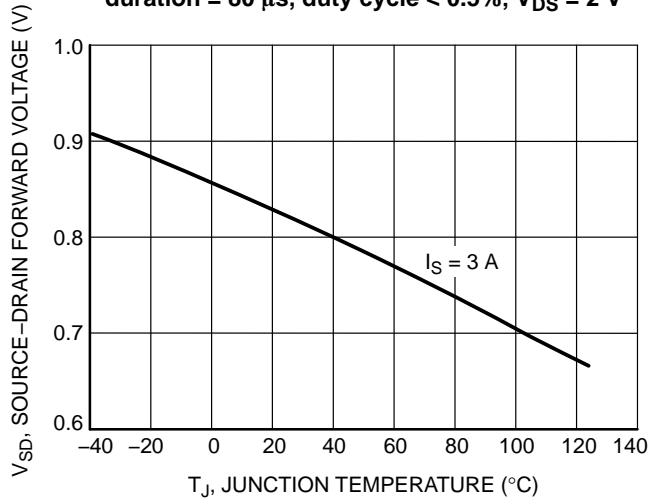


Figure 5. Body Diode Forward Voltage vs. Junction Temperature

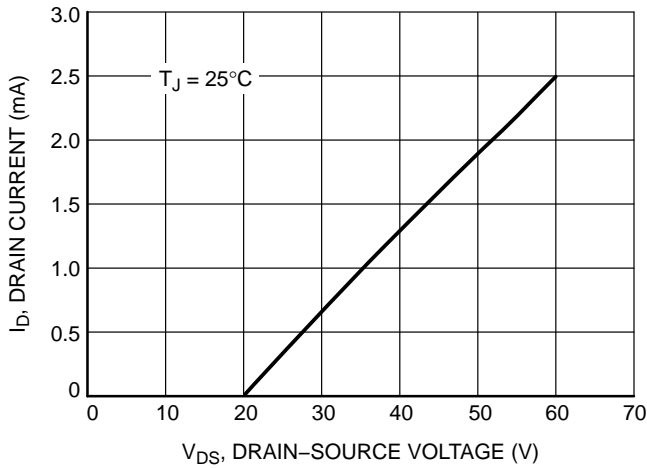


Figure 6. Off-State Drain Current vs. Drain-Source Voltage (includes feedback network current)

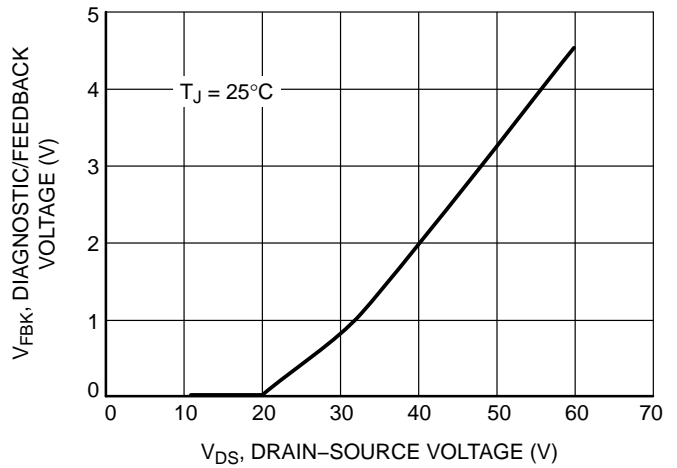


Figure 7. Diagnostic Feedback Voltage vs. Drain-Source Voltage

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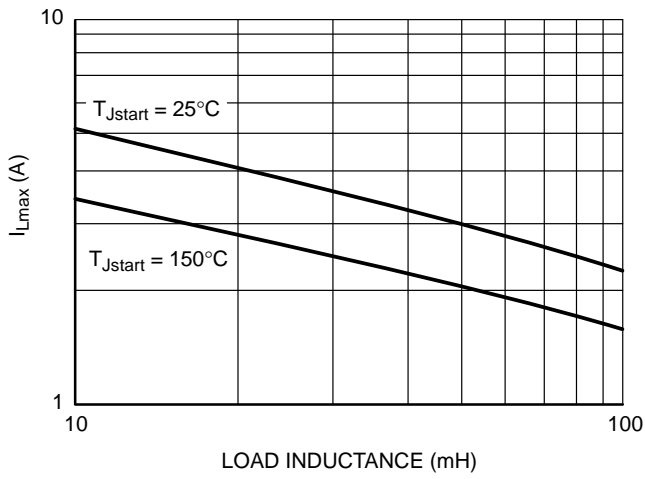


Figure 8. Single Pulse Maximum Switch-off Current vs. Load Inductance

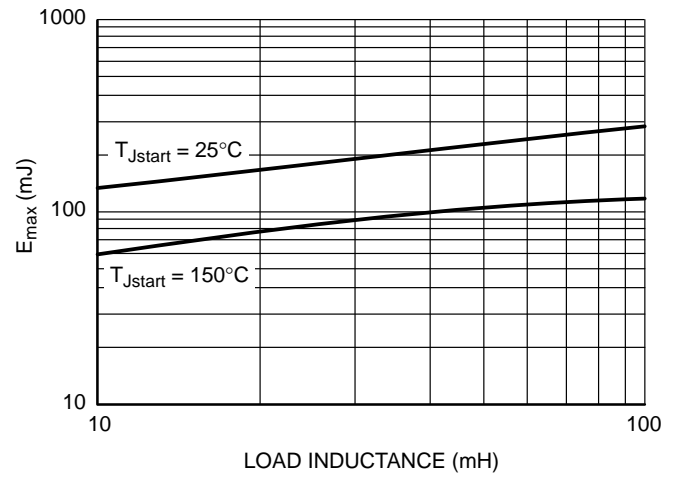


Figure 9. Single Pulse Maximum Switching Energy vs. Load Inductance

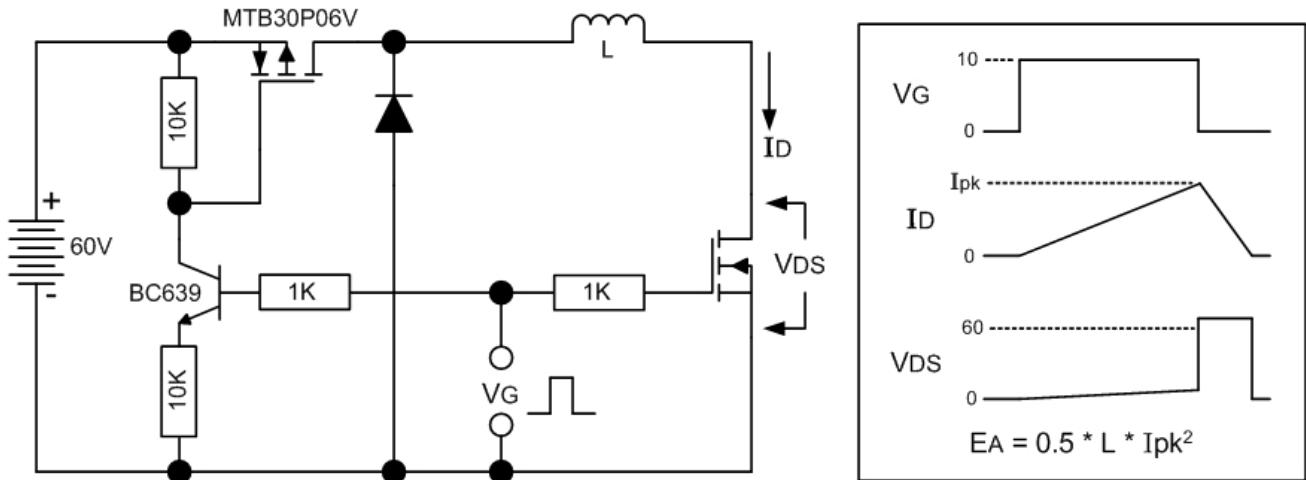


Figure 10. Single Pulse Peak Drain Current and Avalanche Energy Test Circuit

# NIMD6001AN

## TYPICAL THERMAL RESPONSE CHARACTERISTICS

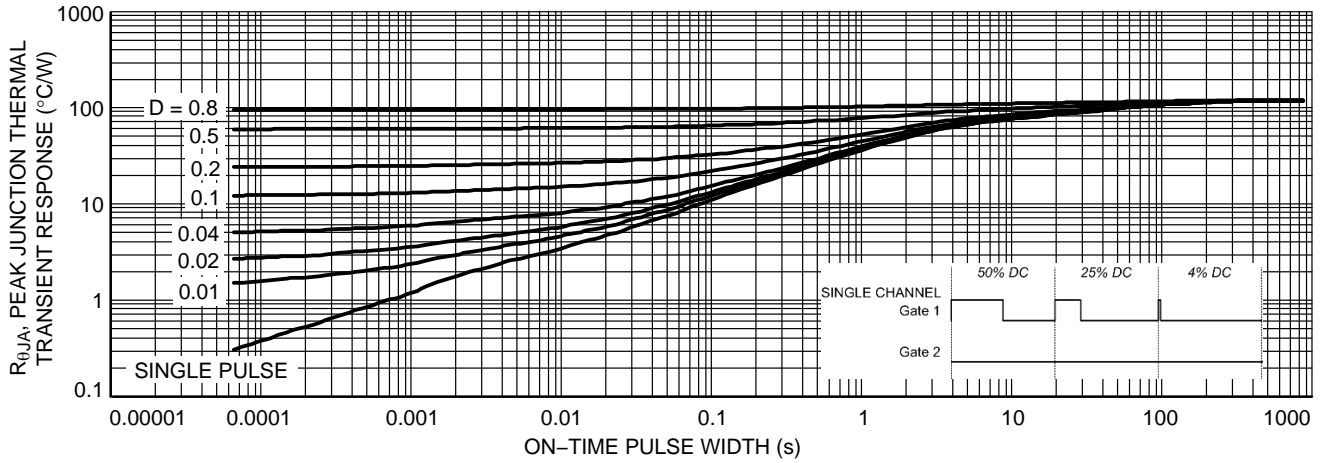


Figure 11. Single Channel Active; Mounted on Minimum-Pad Board

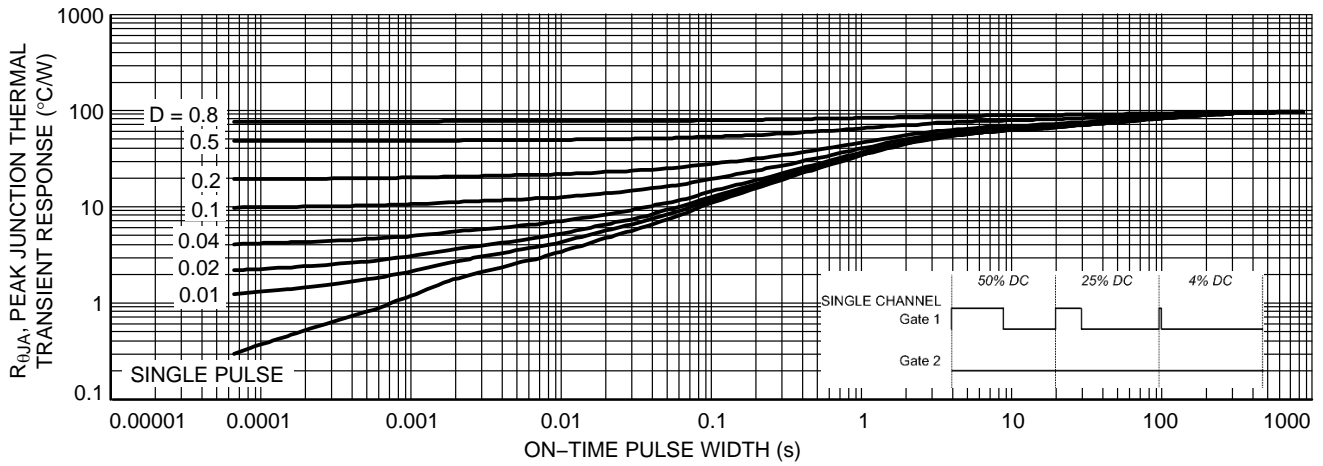


Figure 12. Single Channel Active; Mounted on 1 Sq. Inch Copper Spreader

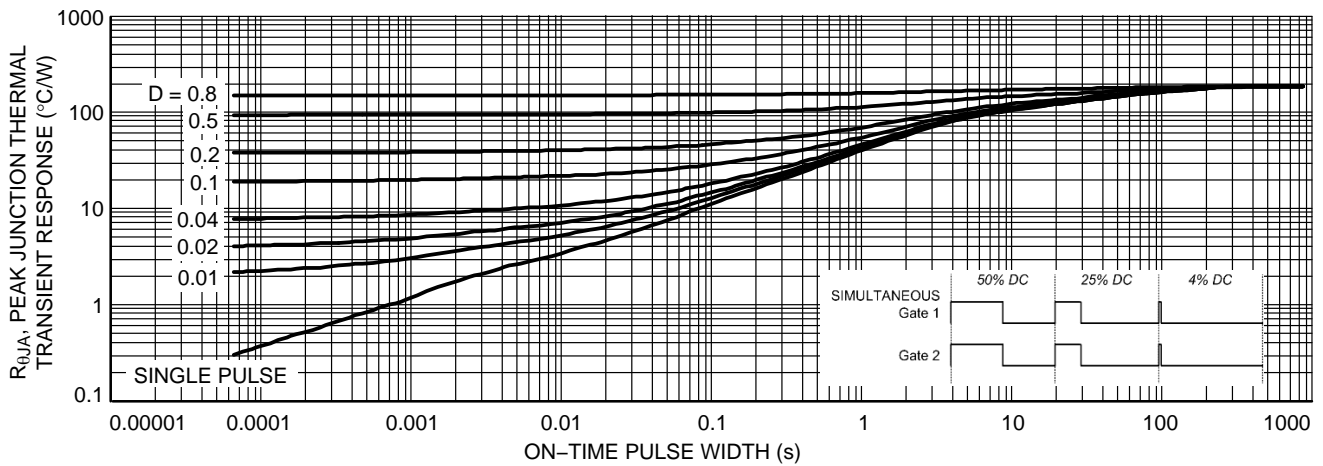


Figure 13. Both Channels Active; Mounted on Minimum-Pad Board

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## TYPICAL THERMAL RESPONSE CHARACTERISTICS

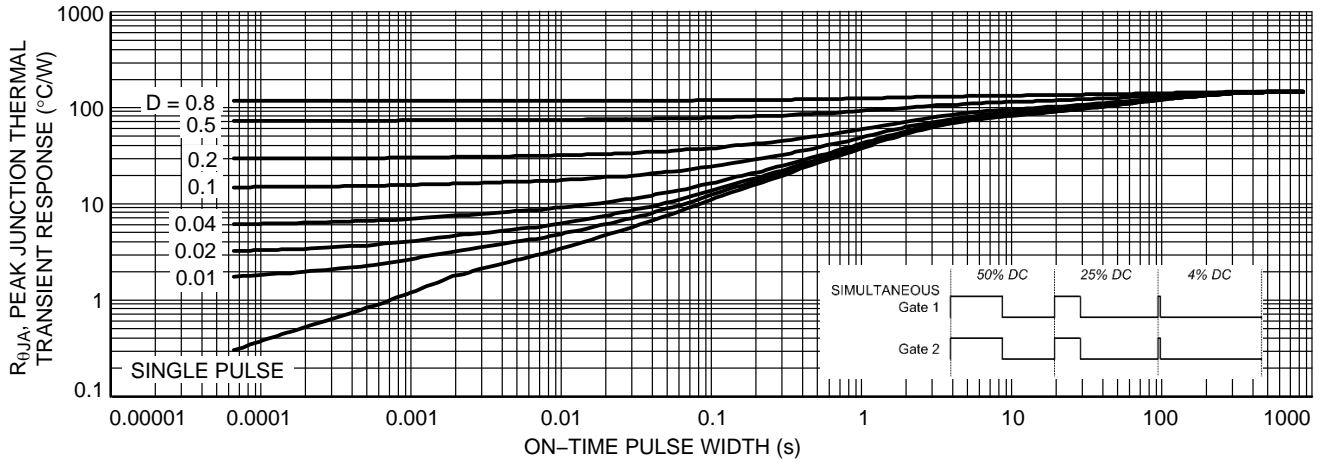


Figure 14. Both Channels Active; Mounted on 1 Sq. Inch Copper Spreader

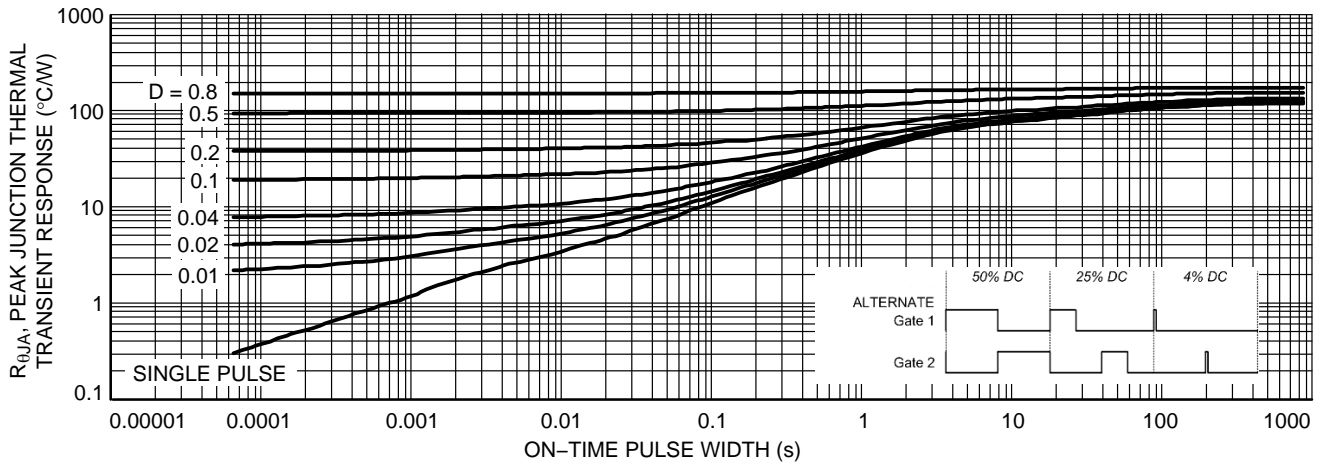


Figure 15. Channels Alternatively Active; Mounted on Minimum-Pad Board

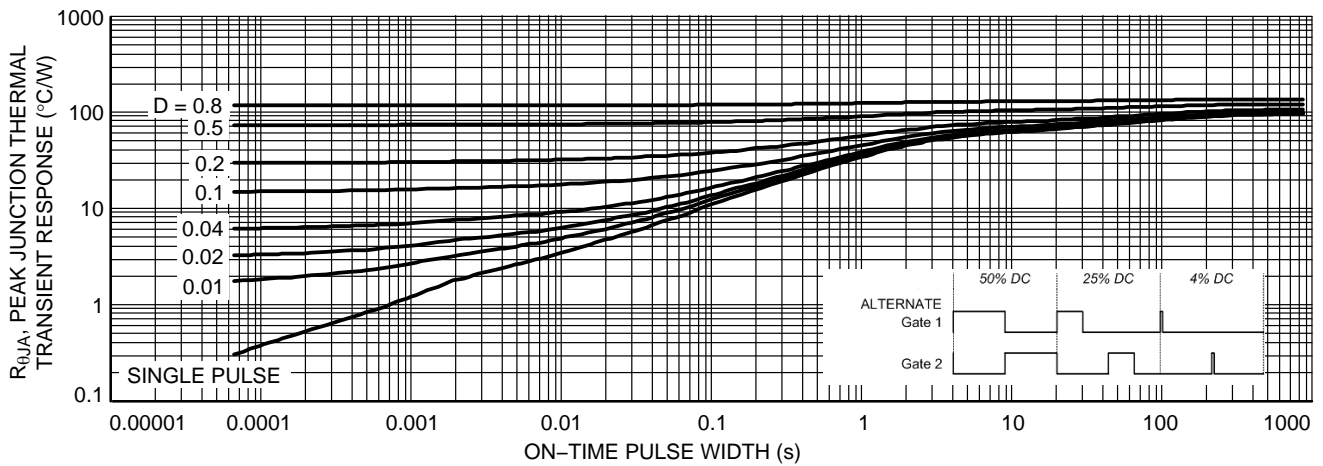
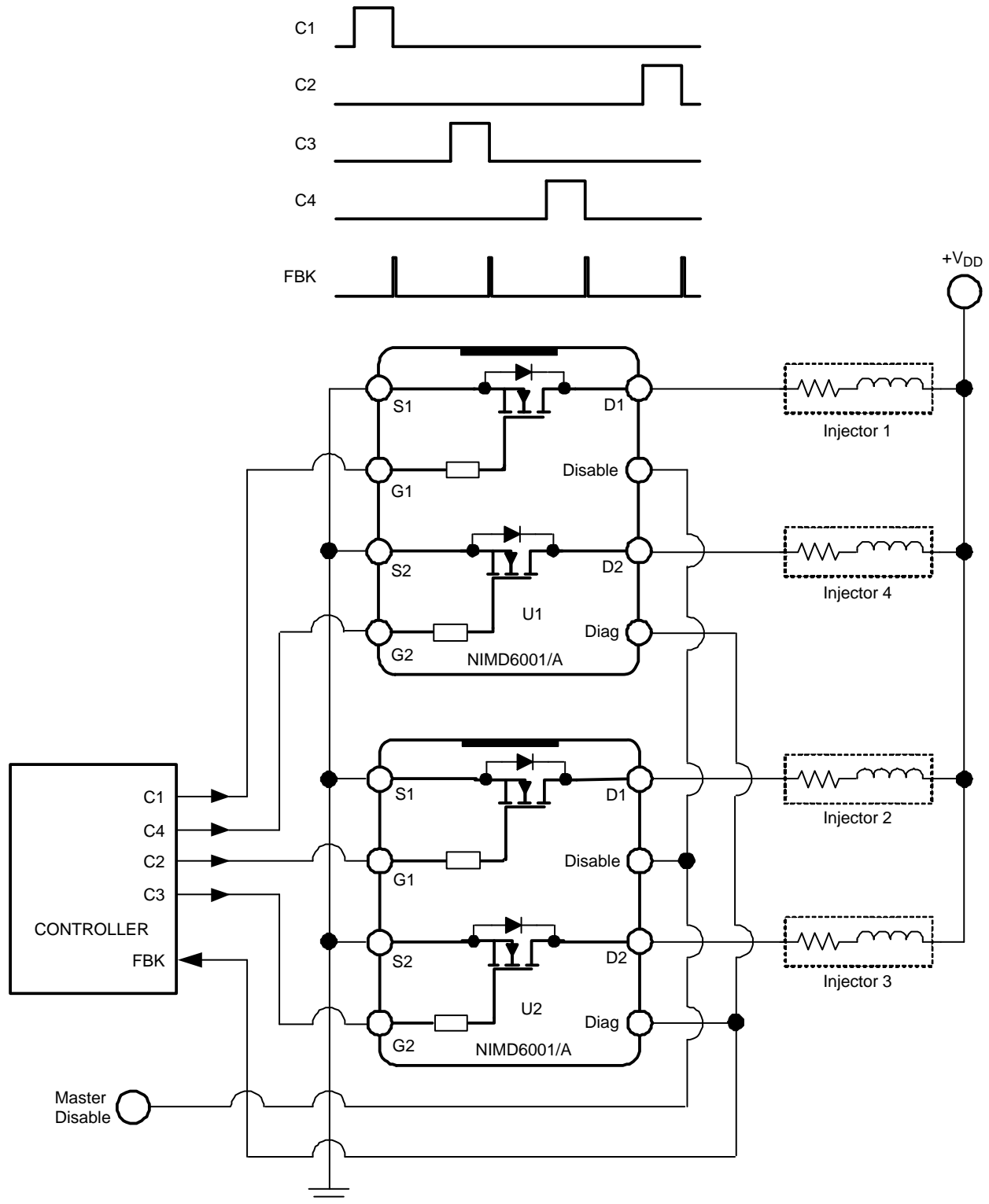


Figure 16. Channels Alternatively Active; Mounted on 1 Sq. Inch Copper Spreader

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## TYPICAL APPLICATION CIRCUIT



**Figure 17. 4 Cylinder Engine Fuel Injection**

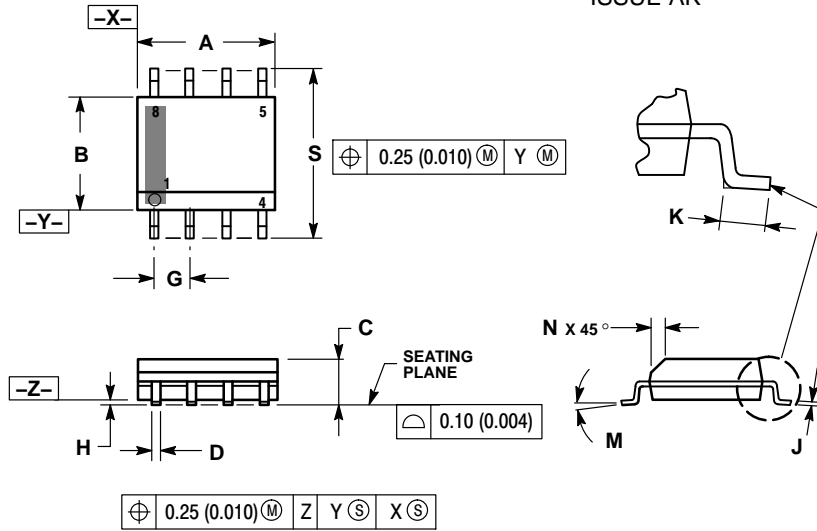
- 4-Cycle engine; 1 injector pulse during intake stroke
- To optimize transient thermal resistance of the NIMD6001/A devices, the injector drive pulses are alternated between U1 and U2.
- Cylinder firing order is 1-3-4-2
- The coincident FBK pulse will be missing if any injector is open or shorted.



# NIMD6001AN

## PACKAGE DIMENSIONS

### SOIC-8 NB CASE 751-07 ISSUE AK

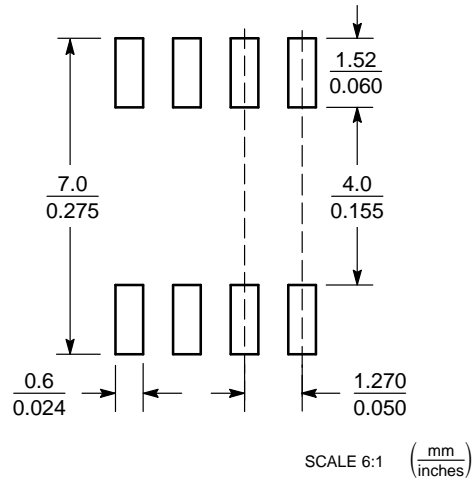


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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